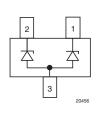


Two-Line ESD Protection in SOT-23





MARKING (example only)



YYY = type code (see table below) XX = date code

DESIGN SUPPORT TOOLS

Models Available



FEATURES

- Two-line ESD protection device
- ESD immunity acc. IEC 61000-4-2
 - ± 30 kV contact discharge
 - ± 30 kV air discharge
- ESD capability according to AEC-Q101: human body model: class H3B: > 8 kV
- Space saving SOT-23 package
- e3 Sn
- AEC-Q101 qualified available
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





RoHS HALOGEN FREE

GREEN (5-2008)

ORDERING INFORMATION								
	ENVIR	ONMENTAL AN	ID QUALITY CO	DDE	PACKAG	ING CODE		
(-)(()	AEC-Q101 QUALIFIED	RoHS-COM LEAD (P	MPLIANT + b)-FREE	TIN PLATED	3K PER 7" REEL (8 mm TAPE),	10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)	
	QUALIFIED	STANDARD	GREEN	PLATED	15K/BOX = MOQ	10K/BOX = MOQ		
GSOT05C-		E		3	-08		GSOT05C-E3-08	
GSOT05C-			G	3	-08		GSOT05C-G3-08	
GSOT05C-	Н	E		3	-08		GSOT05C-HE3-08	
GSOT05C-	Н		G	3	-08		GSOT05C-HG3-08	
GSOT05C-		E		3		-18	GSOT05C-E3-18	
GSOT05C-			G	3		-18	GSOT05C-G3-18	
GSOT05C-	Н	Е		3		-18	GSOT05C-HE3-18	
GSOT05C-	Н		G	3		-18	GSOT05C-HG3-18	

PACKAG	PACKAGE DATA								
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS		
GSOT03C	SOT-23	03C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
		C1G	Green	8.1 mg		(according J-STD-020)	max. 260 °C		
GSOT04C	SOT-23	04C C8G	Standard Green	8.8 mg 8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
GSOT05C	SOT-23	05C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
GS0105C	501-23	C2G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	max. 260 °C		
GSOT08C	SOT-23	08C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
G30106C	301-23	C3G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	max. 260 °C		
GSOT12C	SOT-23	12C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
4301120	301-23	C4G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	max. 260 °C		
GSOT15C	SOT-23	15C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
4301130	301-23	C5G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	max. 260 °C		
GSOT24C	SOT-23	24C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
G301240	301-23	C6G	Green	8.1 mg	OL 34 V-0	(according J-STD-020)	max. 260 °C		
GSOT36C	SOT-23	36C	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature		
4301300	301-23	C7G	Green	8.1 mg	OL 34 V-0	(according J-STD-020)	max. 260 °C		

Rev. 2.7, 04-Jan-2019 Document Number: 85824



ABSOLUTE MAXIMUM RATINGS GSOT03C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Bud a law and	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	1	30	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	.30	Α			
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	369	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	504	W		
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT04C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Deale autor august	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	l	30	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ІРРМ	30	Α		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	429	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	564	W		
CCD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT05C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20~\mu s$; single shot	I	30	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	• •	30	Α		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20~\mu s$; single shot	P_PP	480	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	грр	612	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	W	± 30	kV		
ESD IMMUNITY	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		



ABSOLUTE MAXIMUM RATINGS GSOT08C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
But a large and	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	I	18	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	I _{PPM}	18	А		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	345	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	400	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD IIIIIIIIIIIII	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	T _J	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT12C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
But a law and	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	I	12	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ІРРМ	12	А		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	312	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, t _p = 8/20 µs; single shot	ГРР	337	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	W	± 30	kV		
ESD initiduity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	T _J	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT15C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Post of law or word	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	1	8	Α		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20~\mu s$; single shot	I _{PPM}	8	Α		
Dook pulso power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20~\mu s$; single shot	D	345	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	400	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 30	kV		
ESD IIIIIIIIIIIII	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	T _J	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		



ABSOLUTE MAXIMUM RATINGS GSOT24C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Bulling	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	l	5	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ІРРМ	5	Α		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	· P _{PP}	235	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	240	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
L3D initiditity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD .	± 30	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT36C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	l	3.5	А		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	Іррм	3.5	А		
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	248	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	252	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
LSD initiditity	Air discharge acc. IEC 61000-4-2; 10 pulses	V ESD	± 30	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		



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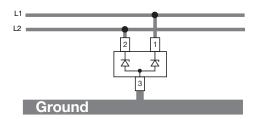
BIAs-MODE (2-line Bidirectional Asymmetrical protection mode)

With the GSOTxxC two signal- or data-lines (L1, L2) can be protected against voltage transients. With pin 3 connected to ground and pin 1 and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified Maximum Reverse Working Voltage (V_{RWM}) the protection diode between pin 2 and pin 3 and between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The Clamping Voltage (V_C) is defined by the breakdown voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low Forward Voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxxC clamping behavior is Bidirectional and Asymmetrical (BiAs).

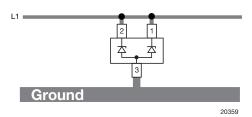




If a higher surge current or peak pulse current (I_{PP}) is needed, both protection diodes in the GSOTxxC can also be used in parallel in order to "double" the performance.

This offers:

- double surge power = double peak pulse current (2 x I_{PPM})
- half of the line inductance = reduced clamping voltage
- half of the line resistance = reduced clamping voltage
- double line capacitance (2 x C_D)
- double reverse leakage current (2 x I_R)



ELECTRICAL CHARACTERISTICS GSOT03C (T_{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3 **PARAMETER TEST CONDITIONS/REMARKS** SYMBOL MIN. UNIT TYP. MAX. Protection paths Number of lines which can be protected N_{channel} _ 2 lines Reverse stand-off voltage Max. reverse working voltage 3.3 ٧ V_{RWM} ٧ Reverse voltage at $I_R = 100 \mu A$ V_R 3.3 Reverse current at $V_R = 3.3 \text{ V}$ I_R _ _ 100 μΑ at $I_R = 1 \text{ mA}$ 4.0 5.5 ٧ Reverse breakdown voltage V_{BR} 4.6 at $I_{PP} = 1 A$ 5.7 7.5 ٧ Reverse clamping voltage V_{C} at $I_{PP} = I_{PPM} = 30 \text{ A}$ 10 12.3 V at $I_{PP} = 1 A$ 1 1.2 ٧ Forward clamping voltage V_F V 4.5 at $I_{PP} = I_{PPM} = 30 \text{ A}$ at $V_R = 0 V$; f = 1 MHz420 600 рF Capacitance C_D at $V_R = 1.6 \text{ V}$; f = 1 MHz260 рF



ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines	
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	4	V	
Reverse voltage	at I _R = 20 μA	V_R	4	-	-	V	
Reverse current	at V _R = 4 V	I _R	-	-	20	μΑ	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	5	6.1	7	V	
Deverse elements voltage	at I _{PP} = 1 A	V	-	7.5	9	V	
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	11.2	14.3	V	
Famous delegas in a college	at I _{PP} = 1 A	.,,	-	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V	
Canacitanas	at V _R = 0 V; f = 1 MHz		-	310	450	pF	
Capacitance	at V _R = 2 V; f = 1 MHz	C _D	-	200	-	pF	

ELECTRICAL CHARACTERISTICS GSOT05C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	5	V		
Reverse voltage	at I _R = 10 μA	V_R	5	-	-	V		
Reverse current	at V _R = 5 V	I _R	-	-	10	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6	6.8	8	V		
Deverse elemning veltage	at I _{PP} = 1 A	V	-	7	8.7	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	12	16	V		
Command alamanian valtana	at I _{PP} = 1 A	V	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V		
Canacitanas	at V _R = 0 V; f = 1 MHz	_	-	260	350	pF		
Capacitance	at V _R = 2.5 V; f = 1 MHz	C _D	-	150	-	pF		

ELECTRICAL CHARACTERISTICS GSOT08C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	8	V		
Reverse voltage	at I _R = 5 μA	V_R	8	-	-	V		
Reverse current	at V _R = 8 V	I _R	-	-	5	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	9	10	11	V		
Deverse elemning veltage	at I _{PP} = 1 A	V	-	10.7	13	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _C	-	15.2	19.2	V		
Forward alamasing valtage	at I _{PP} = 1 A	M	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _F	-	3	-	V		
Canacitanas	at V _R = 0 V; f = 1 MHz		-	160	250	pF		
Capacitance	at V _R = 4 V; f = 1 MHz	C _D	-	80	-	pF		



ELECTRICAL CHARACTERISTICS GSOT12C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	ı	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	12	V		
Reverse voltage	at I _R = 1 μA	V_R	12	-	-	V		
Reverse current	at V _R = 12 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.5	15	16.5	V		
Dayleres slamping valtage	at I _{PP} = 1 A	V	-	15.4	18.7	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _C	-	21.2	26	V		
Famusard alamaning valtage	at I _{PP} = 1 A	V	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _F	-	2.2	-	V		
Conscitores	at V _R = 0 V; f = 1 MHz		-	115	150	pF		
Capacitance	at V _R = 6 V; f = 1 MHz	- C _D	-	50	-	pF		

ELECTRICAL CHARACTERISTICS GSOT15C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	15	V		
Reverse voltage	at I _R = 1 μA	V_R	15	-	-	V		
Reverse current	at V _R = 15 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	16.5	18	20	V		
Deverse elements veltage	at I _{PP} = 1 A	V	-	19.4	23.5	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8 A	V _C	-	24.8	28.8	V		
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 8 A	VF	-	1.8	-	V		
Canacitanas	at V _R = 0 V; f = 1 MHz	_	-	90	120	pF		
Capacitance	at V _R = 7.5 V; f = 1 MHz	C _D	-	35	-	pF		

ELECTRICAL CHARACTERISTICS GSOT24C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	24	V		
Reverse voltage	at I _R = 1 μA	V_{R}	24	-	-	V		
Reverse current	at V _R = 24 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27	30	33	V		
Deverse elemping voltage	at I _{PP} = 1 A	V	-	34	41	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _C	-	41	47	V		
Command alamaina valtaga	at I _{PP} = 1 A		-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _F	-	1.4	-	V		
Conscitores	at V _R = 0 V; f = 1 MHz		-	65	80	pF		
Capacitance	at V _R = 12 V; f = 1 MHz	C _D	-	20	-	pF		

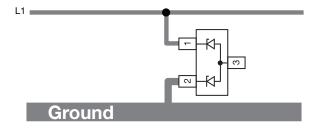


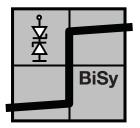
ELECTRICAL CHARACTERISTICS GSOT36C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	36	V		
Reverse voltage	at I _R = 1 μA	V_{R}	36	-	-	V		
Reverse current	at V _R = 36 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	39	43	47	V		
Davaraa alamaina valtaaa	at I _{PP} = 1 A	V	-	49	60	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 3.5 A	V _C	-	59	71	V		
Campand alamania a valta sa	at I _{PP} = 1 A	V	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 3.5 A	V _F	-	1.3	-	V		
Conscitones	at V _R = 0 V; f = 1 MHz		-	52	65	pF		
Capacitance	at V _R = 18 V; f = 1 MHz	C _D	-	12	-	pF		

BISy-MODE (1-line bidirectional symmetrical protection mode)

If a bipolar symmetrical protection device is needed the GSOTxxC can also be used as a single line protection device. Therefore pin 1 has to be connected to the signal- or data-line (L1) and pin 2 to ground (or vice versa). Pin 3 must not be connected. Positive and negative voltage transients will be clamped in the same way. The clamping current through the GSOTxxC passes one diode in forward direction and the other one in reverse direction. The clamping voltage (V_C) is defined by the breakthrough voltage (V_{BR}) level of one diode plus the forward voltage of the other diode plus the voltage drop at the series impedances (resistances and inductances) of the protection device.

Due to the same clamping levels in positive and negative direction the GSOTxxC voltage clamping behaviour is bidirectional and symmetrical (BiSy).





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	ETERISTICS GSOT03C ($T_{amb} = 25$ pin 2 to pin 1; pin 3 not connected	°C unless	otherwise	specified)	
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	3.8	V
Reverse voltage	at I _R = 100 μA	V_R	3.8	-	-	V
Reverse current	at V _R = 3.8 V	I _R	-	-	100	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	4.5	5.3	6.2	V
Develop alamaian vallana	at I _{PP} = 1 A	V	-	7	8.4	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	ı	14	16.8	V
Capacitance	at V _R = 0 V; f = 1 MHz		-	210	300	pF
	at V _R = 1.6 V; f = 1 MHz	- C _D	-	190	-	pF



ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	4.5	V		
Reverse voltage	at I _R = 20 μA	V_R	4.5	-	-	V		
Reverse current	at V _R = 4.5 V	I _R	-	-	20	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	5.5	6.8	7.7	V		
Doverse elemning voltage	at I _{PP} = 1 A	W	-	7.5	9	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	15.7	18.8	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	155	225	pF		
	at V _R = 2 V; f = 1 MHz		-	135	-	pF		

ELECTRICAL CHARACTERISTICS GSOT05C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	=.	-	5.5	V			
Reverse voltage	at I _R = 10 μA	V_R	5.5	-	-	V			
Reverse current	at V _R = 5.5 V	I _R	-	-	10	μΑ			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6.5	7.5	8.7	V			
Deviage elements valtage	at I _{PP} = 1 A	V	=.	8.1	9.7	V			
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	17	20.4	V			
0	at V _R = 0 V; f = 1 MHz	- C _D	-	130	175	pF			
Capacitance	at $V_R = 4 V$; $f = 1 MHz$		-	100	-	pF			

ELECTRICAL CHARACTERISTICS GSOT08C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	8.5	V		
Reverse voltage	at I _R = 5 μA	V_R	8.5	-	-	V		
Reverse current	at V _R = 8.5 V	I _R	-	-	5	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	9.5	10.7	11.7	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	11.7	14	V		
neverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	v _C	-	18.5	22.2	V		
Canacitanas	at V _R = 0 V; f = 1 MHz	0	-	80	125	pF		
Capacitance	at $V_R = 4 V$; $f = 1 MHz$	C _D	=	60	-	pF		

ELECTRICAL CHARACTERISTICS GSOT12C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	12.5	V		
Reverse voltage	at I _R = 1 μA	V_R	12.5	-	-	V		
Reverse current	at V _R = 12.5 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.5	15.7	16.5	V		
Payaraa alamaina valtaga	at I _{PP} = 1 A	W	-	16.4	19.7	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _C	-	23.4	28.1	V		
Canacitanas	at V _R = 0 V; f = 1 MHz	- C _D	-	58	75	pF		
Capacitance	at V _R = 7.5 V; f = 1 MHz		-	36	-	pF		



ELECTRICAL CHARACTERISTICS GSOT15C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	15.5	V		
Reverse voltage	at I _R = 1 μA	V_R	15.5	-	-	V		
Reverse current	at V _R = 15.5 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	17	18.7	20.7	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	20.4	24.5	V		
heverse clamping voltage	at I _{PP} = I _{PPM} = 8 A	VC	-	26.6	30.6	V		
Canacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	45	60	pF		
Capacitance	at V _R = 7.5 V; f = 1 MHz		-	25	-	pF		

ELECTRICAL CHARACTERISTICS GSOT24C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	24.5	V		
Reverse voltage	at I _R = 1 μA	V_R	24.5	-	-	V		
Reverse current	at V _R = 24.5 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27.5	30.7	33.7	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	34	41	V		
neverse clamping voltage	at $I_{PP} = I_{PPM} = 5 A$	VC	-	40	48	V		
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	- C _D	-	33	40	pF		
	at V _R = 12 V; f = 1 MHz		-	18	-	pF		

ELECTRICAL CHARACTERISTICS GS0T36C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	36.5	V
Reverse voltage	at I _R = 1 μA	V_R	36.5	-	-	V
Reverse current	at V _R = 36.5 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	39.5	43.7	47.7	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	50	60	V
	at I _{PP} = I _{PPM} = 3.5 A		-	60	72	V
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	C _D	-	26	33	pF
	at V _R = 18 V; f = 1 MHz		-	10	-	pF



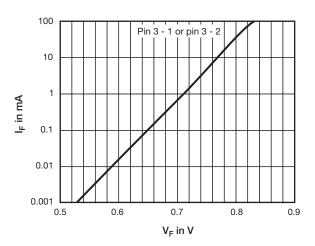


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

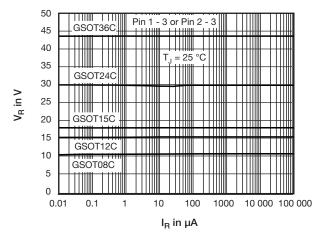


Fig. 2 - Typical Reverse Voltage V_R vs. Reverse Current I_R

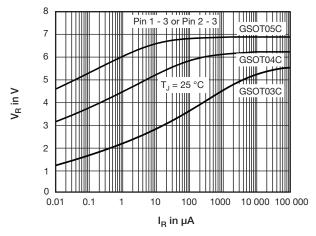
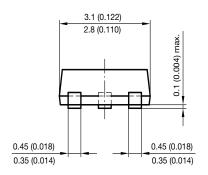
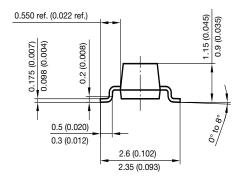
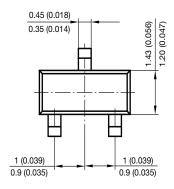


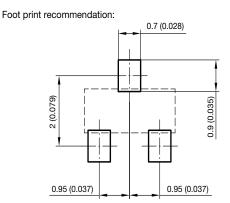
Fig. 3 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

PACKAGE DIMENSIONS in millimeters (inches): SOT-23

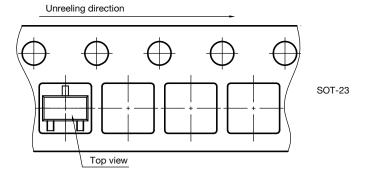








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Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607



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